135 # 3 頁 第 1 頁 國立成功大學九十九學年度碩士班招生考試試題

系所組別: 工程科學系甲、戊、已組

緩跳

電子電路 考試科目 新秋日期:0307·新次:1

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1. In Fig. 1, the diodes and the op-amp are ideal. (a) Plot the transfer characteristic. (6 分) (b) Plot the waveform of V_O when $V_f = 15\sin(4\pi t)$. (5 %)

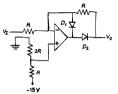
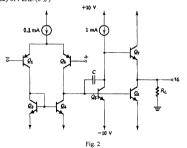


Fig. 1

Figure 2 shows a circuit suitable for op-amp application. For all transistors β=100, V_{RE}=0.7 V.

 $|V_r| = 25$ mV, and $r_a = \infty$. (a) For inputs grounded and output held at 0 V, find the emitter currents of all transistors (you can ignore base currents for dc analysis). (4 分) (b) Calculate the gain of the amp with a load of 10 kΩ. (8 分) (c) With load as in (b), calculate the value of the capacitor C required for a 3-dB frequency of 1 kHz. (6 分)



(背面仍有題目.請繼續作答)

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3. Analyze the circuit in Fig. 3. The transistors are biased by a current source such that the transistors have β=100, r_s=5 kΩ, g_s=20 mA/V, r_s=∞, C_s=2 pF, and C_s=6 pF (a) Find the midband gain: (7 %) (b) Find f_{tt} by using the open-circuit time constant • (8 %)

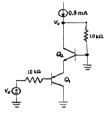


Fig. 3

4. For the diff. amp in Fig. 4, (a) Sketch the differential half-ckt and the common-mode half-ckt. (8 分) (b) Find the differential gain, the differential input resistance, the common-mode gain, and the common-mode input reistance. Assume that β = 100, V_f=25 mV, and V_s = ∞. (12 分) +15 V

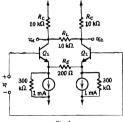


Fig. 4

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 In Fig. 5, the transistors are assumed to have common-emitter current gain β, emitter resistance r_e, and early voltage V_A=∞. Find expressions for A_f ≡ v_g/v_g, R_B, and R_{mg}. (20 分)

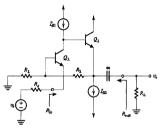


Fig. 5

6. In Fig. 6, an approach realizing the OR function of six input variables is shown. (a) Sketch the CMOS realization for the logic gates in the figure · (6 %) (b) Assuming that the transistors in the circuit are properly sized to provide each gate with a current-driving capability equal to that of the basic matched inverter, find the number of transistors and the total area. Assume that the basic inverter has the (W/L)_n ratio of 1.2 µm / 0.8 µm and the (W/L)_n ratio of 3.6 µm / 0.8 µm * (10 %)

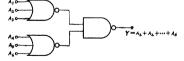


Fig. 6